

TF2136M

3-Phase Half-Bridge Gate Driver

Features

- Three floating high-side drivers in bootstrap operation to 600V
- 200mA source / 350mA sink output current capability
- Outputs tolerant to negative transients, dV/dt immune
- Wide VCC operating range: 10V to 20V
- Logic input 3.3V capability
- Internal deadtime of 290ns to protect MOSFETs
- Matched prop delay for all channels
- Outputs out of phase with inputs
- Schmitt triggered logic inputs
- Cross conduction prevention logic
- Undervoltage lockout for all channels
- Overcurrent protection shuts down drivers

Applications

- 3-Phase Motor Inverter Driver
- White Goods Air Conditioner, Washing Machine, Refrigerator
- Industrial Motor Inverter Power Tools, Robotics
- General Purpose 3-Phase Inverter

Description

The TF2136M is a three-phase gate driver IC designed for high voltage, high speed applications, driving N-channel MOSFETs and IGBTs in a half-bridge configuration. TF Semiconductor's high voltage process enables the TF2136M high sides to switch to 600V in a bootstrap operation.

The TF2136M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices and are enabled low to better function in high noise environments. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The TF2136M offers numerous protection functions. A shoot-through protection logic prevents both outputs being high with both inputs high (fault state), an undervoltage lockout for $V_{\rm CC}$ shuts down all drivers through an internal fault control, and a UVLO for $V_{\rm BS}$ shuts down the respective high side output. Also an overcurrent protection will terminate the six outputs. Both the $V_{\rm CC}$ UVLO and the overcurrent protection trip an automatic fault clear with a timing that is adjustable with an external capacitor.

The TF2136M is offered in SOIC 28 package and operates over an extended -40 °C to +125 °C temperature range.

SOIC-28



Ordering Information

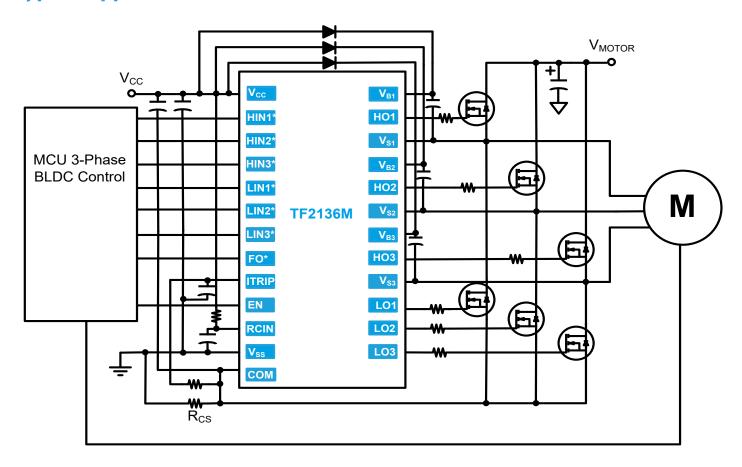
Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF2136M-TLS	SOIC-28	Tube / 25	YYWW
TF2136M-TLH	SOIC-28	T&R / 1500	TF2136M Lot ID

www.tfsemi.com Rev. 1.2

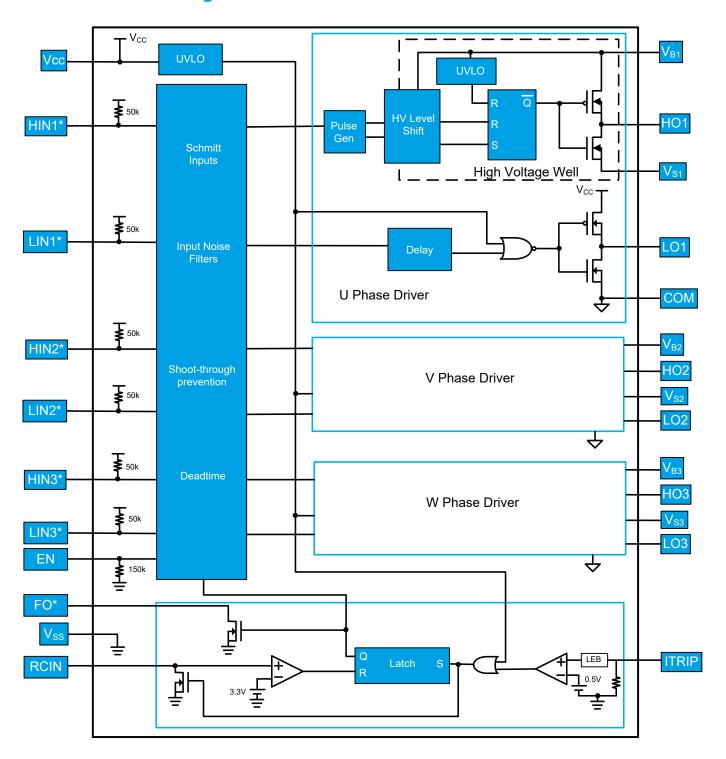


Typical Application

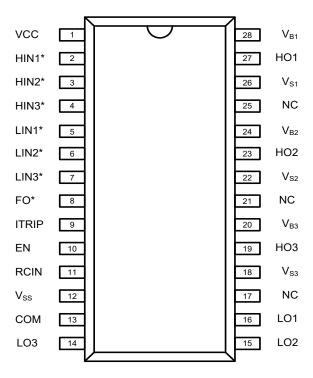




Functional Block Diagram







Top View: SOIC-28

Pin Descriptions

PIN NAME	PIN NUMBER	PIN DESCRIPTION
VCC	1	Low-side and logic fixed supply
HIN1*, HIN2*, HIN3*	2, 3, 4	Logic input for high-side gate driver output, out of phase with HO.
LIN1*, LIN2*, LIN3*	5, 6, 7	Logic input for low-side gate driver output, out of phase with LO.
FO*	8	Fault output with open drain (fault with over-current and VCC UVLO)
ITRIP	9	Analog input for over-current shutdown
EN	10	Logic input for functionality, I/O logic functions when EN is high.
RCIN	11	An external RC network input used to define FAULT CLEAR delay
V _{ss}	12	Logic ground
COM	13	Low-side driver return
LO3, LO2, LO1	14, 15, 16	Low-side gate driver output
NC	17, 21, 25	No Connect
V _{S3} ,V _{S2} ,V _{S1}	18, 22, 26	High-side floating supply return
HO3, HO2, HO1	19, 23, 27	High-side gate driver output
V _{B3} ,V _{B2} ,V _{B1}	20, 24, 28	High-side floating supply



Absolute Maximum Ratings (NOTE1)

V _B - High-side floating supply voltage	0.3V to +624V
V _s - High-side floating supply offset voltage.	V_{B} -24V to V_{B} +0.3V
V_{HO} - High-side floating output voltage	V_{s} -0.3VtoV _B +0.3V
V ₁₀ - Low-side output voltage	0.3V to V_{cc} +0.3V
dV _s /dt-Offset supply voltage transient	50 V/ns
V _{cc} - Low-side fixed supply voltage	0.3V to +24V
VLogic input voltage(HIN*,LIN*,ITRIP,ENanc	

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

3-Phase Half-Bridge Gate Drive

P_D - Package power dissipation at $T_A \le 25$ °C SOIC-28	2.3W
SOIC-28 Thermal Resistance (NOTE2)	
θ_{IC}	45 °C/W
θ_{JA}	
T _J - Junction operating temperature	+150 °C
T _L - Lead Temperature (soldering, 10 seconds)	+300°C
T _{sta} - Storage temerature	55 to 150 °C

NOTE2 Thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
$V_{\scriptscriptstyle B}$	High side floating supply absolute voltage	V _s + 10	V _s + 20	V
V _s	High side floating supply offset voltage	NOTE3	600	V
V _{HO}	High side floating output voltage	V _s	V _B	V
V _{CC}	Low side fixed supply voltage	10	20	V
V _{LO}	Low side output voltage	COM	V _{cc}	V
V _{IN}	Logic input voltage (HIN*, LIN*, ITRIP, EN)	V _{ss}	5	V
V _{FO}	Fault output Voltage	V _{ss}	V _{cc}	V
V _{ss}	Logic Ground	-5	5	С
T _A	Ambient temperature	-40	125	°C

NOTE3 Logic operational for VS of -5V to +600V.



DC Electrical Characteristics (NOTE4)

3-Phase Half-Bridge Gate Driver

 $\rm V_{BIAS}(\rm V_{CC}, \rm V_{BS}\,) = 15V, \rm T_A = 25~^{\circ}C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V _{IH}	Logic "0" input voltage		2.4			
V _{IL}	Logic "1" input voltage				0.8	
V _{OH}	High level output voltage, V _{BIAS} - V _O	$I_0 = 0 \text{mA}$			0.1	V
V _{OL}	Low level output voltage, V _o	$I_0 = 0 \text{mA}$			0.1	
I _{LK}	Offset supply leakage current	VB = VS = 600V			10	
I _{BSQ}	Quiescent V _{BS} supply current	V _{IN} = 0V or 5V, EN=0V	10	85	130	μΑ
I _{ccq}	Quiescent V _{CC} supply current	V _{IN} = 0V or 5V, EN=0V		1.1	1.6	mA
I _{IN+}	Logic input bias current (HO=LO=HIGH)	V _{IN} = 0V		130	200	
I _{IN-}	Logic input bias current (HO=LO=LOW)	V _{IN} = 5V		3.0	20	μΑ
I _{EN+}	Logic Enable "1" input bias current	V _{EN} = 5V		33	80	μА
I _{EN-}	Logic Enable "0" input bias current	V _{EN} = 0V			2	μА
$V_{\text{BSUV+}}$ $V_{\text{CCUV+}}$	V_{BS} and V_{CC} supply under-voltage positive going threshold		7.6	8.9	9.9	
V _{BSUV} -	$V_{\rm BS}$ and $V_{\rm CC}$ supply under-voltage negative going threshold		7.1	8.3	9.4	V
I _{O+}	Output high short circuit pulsed current	$V_O = 0V$, PW $\leq 10 \mu s$	120	200		
I _{O-}	Output low short circuit pulsed current	$V_0 = 15V, PW \le 10 \ \mu s$	250	350		mA
V _{ITH+}	Overcurrent detect positive threshold		400	500	600	mV
V _{ITH} -	Overcurrent detect negative threshold		340	420	500	mV
I _{CSIN}	Short-circuit input current	V _{CSIN} =1V	6.0	11	16	μА
$V_{RCINTH+}$	RCIN Positive going threshold voltage		7.0	8.4	9.8	V
V _{RCINTH} -	RCIN Negative going threshold voltage			5		V
V _{FOL}	Fault output low level voltage	V _{CS} =1V, I _{FO} =1.5mA		0.2	0.5	V
R _{DSRCIN}	RCIN On resistance	I _{RCIN} =1.5mA	40	75	110	Ω
R _{DSFO}	Fault output on resistance	I _{FO} =1.5mA	80	130	180	Ω

NOTE4 The V_{NV} V_{THY} and I_{NN} parameters are referenced to V_{SS} and are applicable to all six channels (HIN1,2,3* and LIN1,2,3*). The V_0 and I_0 parameters are applicable to the outputs (H01,2,3 and L01,2,3 and are referenced to COM.

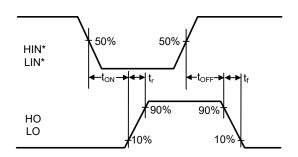


AC Electrical Characteristics

 $\rm V_{BIAS}(V_{CC},V_{BS})$ = 15V, $\rm C_L$ = 1000pF, and $\rm T_A$ = 25 $^{\circ}\rm C$, unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	мах	Unit
t _{on}	Turn-on propogation delay	$V_s = 0V$	200	330	460	
t _{off}	Turn-off propogation delay	$V_s = 0V$	200	330	460	ns
t _r	Turn-on rise time			90	150	
t _f	Turn-off fall time	$V_s = 0V$		35	60	
t _{DM}	Delay matching				50	ns
t _{EN}	Enable low to output shutdown delay		225	330	425	ns
t _{BLT}	ITRIP Pin leading-edge blanking time		200	300	400	ns
t _{FLT}	Time from ITRIP triggering to FO*	From V _{ITRIP} = 1V to FO* turn off	360	550	760	ns
t _{ITRIP}	Time from ITRIP triggering to all gate outputs turn off	From V _{ITRIP} = 1V to starting gate turn off	420	615	820	ns
t _{FLTIN}	Input filtering time (HIN*, LIN*, EN)			250		ns
t _{FLTCLR}	Fault clear time	$C_{RCIN} = 1 nF, R_{RCIN} = 2 M\Omega$		1.6		ms
t _{DT}	Deadtime		200	290	420	ns
t _{DTM}	Deadtime matching				50	ns
t _{PM}	Output pulse width matching (NOTES)	PW _{IN} >1μs		50	75	ns

NOTE5 t_{PM} is defined as PW_{IN} - PW_{OUT} .



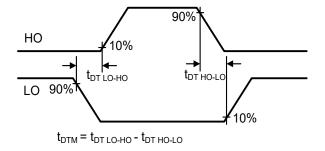


Figure 1. Switching Time Waveform Definitions

Figure 2. Deadtime Waveform Definitions

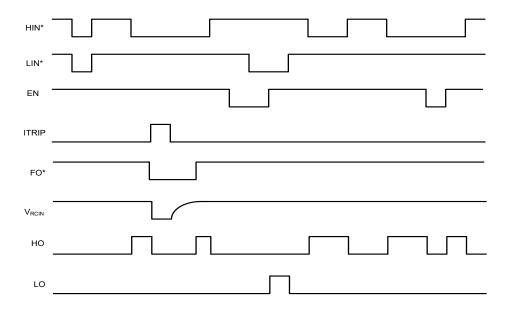


Figure 3. Input/Output Timing Diagram

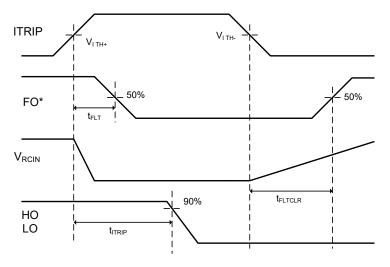
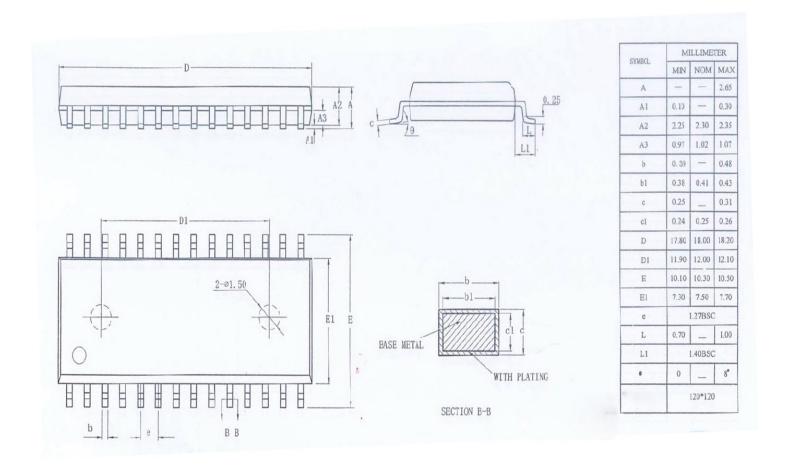


Figure 4. Overcurrent Timing Definitions

Package Dimensions (SOIC-28)

3-Phase Half-Bridge Gate Driver

Please contact support@tfsemi.com for package availability.





Rev.	Change	Owner	Date
1.0	First release AI datasheet	Keith Spaulding	3/12/2018
1.1	VCC Supply ROC edit	Keith Spaulding	7/11/2018
1.2	VCC Supply 10V - 20V	Keith Spaulding	11/14/2018

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